

SEMICONDUCTOR DEVICE AND METHOD FOR FORMING SAME USING MULTI-LAYERED HARD MASK

ABSTRACT OF THE DISCLOSURE

5 According to some embodiments of the invention, bit lines are formed using a multi-layered hard mask and BC nodes are separated by forming line-type BCs in the same direction of gate lines. Thus, a narrowing of shoulders between the bit lines and the BCs can be prevented, and spacers can be formed of a low k-dielectric silicon oxide, thereby lowering parasitic capacitance.